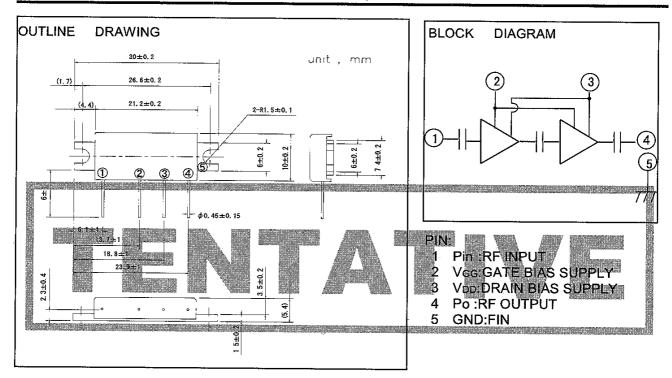
ATTENTION
OBSERVE PRECAUTIONS
FOR HANDLING
ELETROSTATIC
SENSITIVE
DEVICES

MITSUBISHI RF POWER MODULE

RA03M8087M

Silicon MOS FET Power Amplifier, 806-870MHz 3.6W PORTABLE RADIO



Revision date: 26th/Apr. '02

MAXIMUM RATINGS (Tc=25deg.C UNLESS OTHERWISE NOTED)

SYMBOL	PARAMETER	CONDITIONS	RATINGS	UNIT
V _{DD}	SUPPLY VOLTAGE	Zg=Zl=50ohm	9.2	V
Vgg	GATE BIAS VOLTAGE	VDD<7.2V,Pin=0mW,Zg=Zl=50ohm	4	V
Pin	INPUT POWER	f=806-870MHz,Zg=Zl=50ohm	70	mW
Po	OUTPUT POWER	f=806-870MHz,Zg=ZI=50ohm	5	W
Tc(OP)	OPERATION CASE TEMPERATURE	f=806-870MHz,Zg=ZI=50ohm	-30 to +110	deg.C
Tstg	STORAGE TEMPERATURE		-40 to +110	deg.C

Note: Above parameters are guaranteed independently.

ELECTRICAL CHARACTERISTICS (Tc=25deg.C,Zg=ZI=50ohm UNLESS OTHERWISE NOTED)

SYMBOL	PARAMETER	CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
f	FREQUENCY RANGE		806		870	MHz
Po	OUTPUT POWER	Vdd=7.2V, Vgg=3.5V, Pin=50mW	3.6			W
Et	TOTAL EFFICIENCY	Po=3W(Vgg=adjust), Vdd=7.2V, Pin=50mW,	32			%
	2nd HARMONIC				-30	dBc
	INPUT VSWR				4	
		Zg=50ohm, Vdd=4 – 9.2V, LOAD VSWR = 4:1, Pin=25 – 75mW, Po<5W(Vgg Control)	No parasitic oscillation			
		Vdd=9.2V, Pin=50mW, Po=3.6W(Vgg Control), Zg=50ohm, LOAD VSWR = 20:1	No degradation or destroy		-	

ABOVE PARAMETERS, RATINGS, LIMITS AND CONDITIONS ARE SUBJECT TO CHANGE .

-Keep safety first in your circuit designs!

Mitsubishi Electric Corporation puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage. Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of non-flammable material or (iii) prevention against any malfunction or mishap.